

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	1116	438/464.ccls.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 05:18
2	BRS	L2	11437 2	(dielectric near25 substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 05:18
3	BRS	L3	17278	(dielectric near25 substrate) near25 (opening or hole or recess or aperture or via)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 05:19

	Type	L #	Hits	Search Text	DBs	Time Stamp
4	BRS	L4	15492	(dielectric near15 substrate) near15 (opening or hole or recess or aperture or via)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 05:19
5	BRS	L5	623	(dielectric near15 substrate) near15 (opening or hole or recess or aperture or via) near15 (barrier)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 05:34
6	BRS	L6	32	(dielectric near15 substrate) near15 (opening or hole or recess or aperture or via) near15 (barrier) near15 (seed)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 05:42

	Type	L #	Hits	Search Text	DBs	Time Stamp
7	BRS	L7	5	(oxide\$1 near15 substrate) near15 (opening or hole or recess or aperture or via) near15 (barrier) near15 (seed)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 05:41
8	BRS	L8	7	(dielectric) near15 (oxide) near15 (opening or hole or recess or aperture or via) near15 (barrier) near15 (seed)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 05:46
9	BRS	L9	49	(oxide) near15 (opening or hole or recess or aperture or via) near15 (barrier) near15 (seed)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 05:46

	Type	L #	Hits	Search Text	DBs	Time Stamp
10	BRS	L10	7	(metal near oxide) near15 (opening or hole or recess or aperture or via) near15 (barrier) near15 (seed)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 05:55
11	BRS	L11	273	(oxide) near15 (opening or hole or recess or aperture or via) near15 (seed)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 05:55
12	BRS	L12	47	(oxide) near15 (opening or hole or recess or aperture or via) near15 (seed) near15 (barrier)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 06:04

	Type	L #	Hits	Search Text	DBs	Time Stamp
13	BRS	L13	22163	(oxide) near15 (barrier)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 06:05
14	BRS	L14	20	(second near metal near oxide) near15 (barrier)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 06:07
15	BRS	L15	3	(second near metal near oxide) near15 (seed)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 06:08

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L17	0	(second near oxide) near15 (seed) near5 (barrier)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 06:08
17	BRS	L18	0	(second near oxide) near15 (seed) near15 (barrier)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 06:08
18	BRS	L19	0	(second near oxide) near15 (seed) near25 (barrier)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 06:09

	Type	L #	Hits	Search Text	DBs	Time Stamp
19	BRS	L20	3	(second near3 oxide) near15 (seed) near25 (barrier)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 06:09
20	BRS	L21	4	(second near oxide) near15 (seed) near15 (substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 06:09
21	BRS	L16	46	(second near oxide) near15 (seed)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 06:12

	Type	L #	Hits	Search Text	DBs	Time Stamp
22	BRS	L22	3672	(oxide) near15 (seed)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 06:12
23	BRS	L23	211	(oxide) near15 (seed) near15 (barrier)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 06:12
24	BRS	L24	32	(oxide) near15 (seed) near15 (barrier) near15 (substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 06:16

	Type	L #	Hits	Search Text	DBs	Time Stamp
25	BRS	L25	32	(oxide or o2) near15 (seed) near15 (barrier) near15 (substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 06:16
26	BRS	L26	0	(o2) near15 (seed) near15 (barrier) near15 (substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 06:16
27	BRS	L27	0	(O2) near15 (seed) near15 (barrier) near15 (substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 06:17

	Type	L #	Hits	Search Text	DBs	Time Stamp
28	BRS	L29	48	(metal near oxide) near15 (seed) near15 (substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 06:17
29	BRS	L28	569	(oxide) near15 (seed) near15 (substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 06:18

	U	1	Document ID	Title	Current OR
1			US 20040055880 A1	Sidewall magnet improving uniformity of inductively coupled plasma and shields used therewith	204/298.06
2			US 20020088117 A1	Chromium adhesion layer for copper vias in low-k technology	29/852
3			US 6734559 B1	Self-aligned semiconductor interconnect barrier and manufacturing method therefor	257/751
4			US 6649513 B1	Copper back-end-of-line by electropolish	438/626
5			US 6539625 B2	Chromium adhesion layer for copper vias in low-k technology	29/846
6			US 6383929 B1	Copper vias in low-k technology	438/687
7	X		KR 2003002896 A	Method for manufacturing capacitor	

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